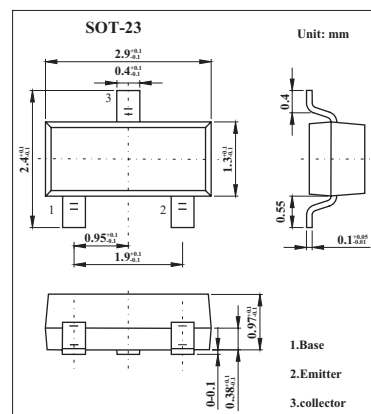


General Purpose Transistor

2SD2226K

■ Features

- High DC current gain.
- High emitter-base voltage.
- Low saturation voltage.



■ Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	60	V
Collector-emitter voltage	V _{CEO}	50	V
Emitter-base voltage	V _{EB0}	12	V
Collector current	I _C	0.15	A
		0.2 *	
Collector power dissipation	P _C	0.2	W
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	-55 to +150	°C

* Single pulse P_w=100ms.

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	BV _{CB0}	I _C =10μA	60			V
Collector-emitter breakdown voltage	BV _{CEO}	I _C =1mA	50			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =10μA	12			V
Collector cutoff current	I _{CB0}	V _{CB} =50V			0.3	μA
Emitter cutoff current	I _{EB0}	V _{EB} =12V			0.3	μA
Collector-emitter saturation voltage *	V _{CE(sat)}	I _C /I _B =50mA/5mA			0.3	V
DC current transfer ratio *	h _{FE}	V _{CE} =5V, I _C =1mA	820		2700	
Output capacitance *	f _T	V _{CE} =5V, I _E =-10mA, f=100MHz		250		MHz
Transition frequency	C _{ob}	V _{CB} =5V, I _E =0, f=1MHz		3.5		pF

* Measured using pulse current.

■ hFE Classification

Marking	BJ	
	V	W
hFE	820~1800	1200~2700